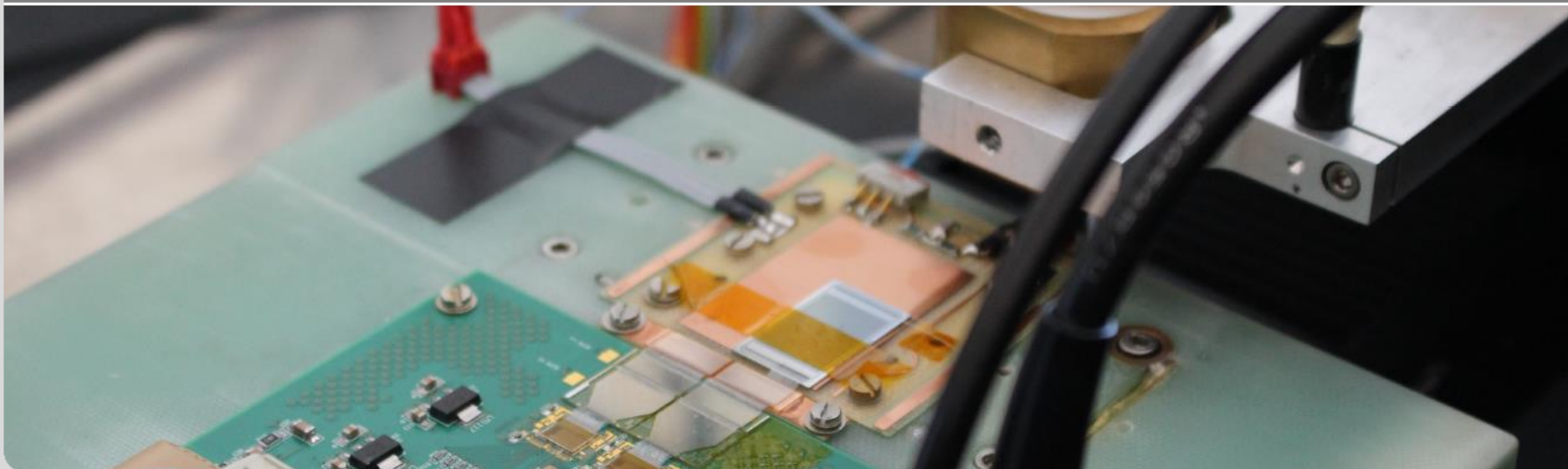


Silicon Sensor Studies within the Scope of the Phase-2 Upgrade of the CMS Outer Tracker

KSETA Workshop 2019 – Marius Metzler

Institut für Experimentelle Teilchenphysik (ETP)



HL-LHC Upgrade in a Nutshell

■ What do we want?

More interesting data



More significant
statistics /
decrease uncertainties



Decrease amount of time
we need for that to happen



Expand physics
potential



■ How do we achieve that?

Accelerator upgrades



Higher luminosity



Detector upgrades



CMS Phase-2 Upgrade

■ New frame-conditions

Higher pile-up



Higher data output



Higher radiation levels



Efficient and reliable
performance for at least
10 years

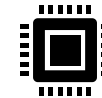


■ Solutions

Increase of sensor granularity



Transition from analog to binary
read-out of channels



Introduction of low-level data filter



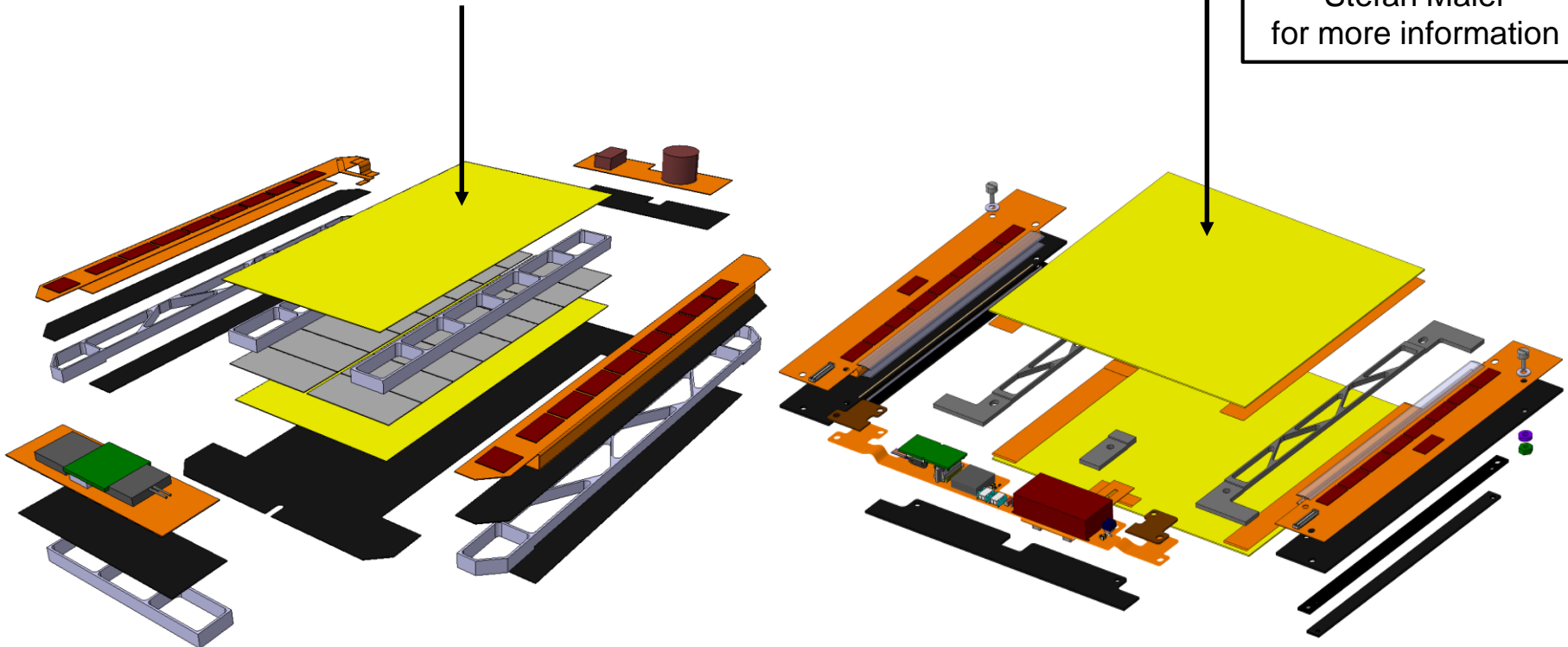
Production of radiation-harder
sensors and electronics



Phase-2 Outer Tracker Modules

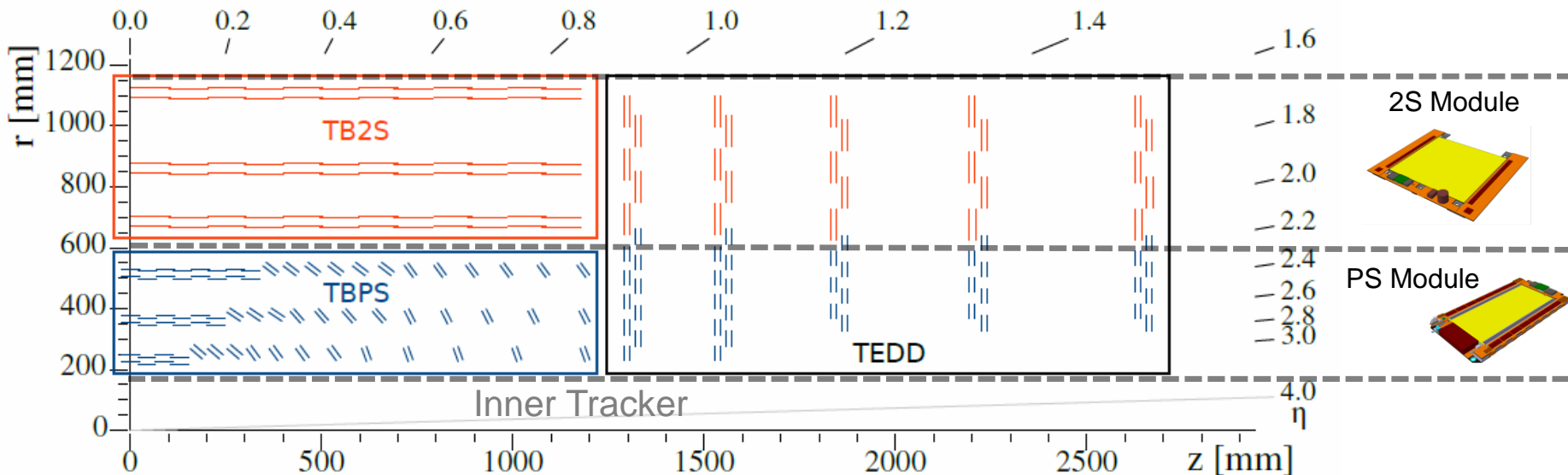
- New module concept with 2 sensors on top of each other
- 2 module types:
 - 2S (2 strip sensors)
 - PS (macro pixel + strip sensor)

Check-out
presentation by
Stefan Maier
for more information



Phase-2 Outer Tracker Modules

- New module concept with 2 sensors on top of each other
- 2 module types:
 - 2S (2 strip sensors)
 - PS (macro pixel + strip sensor)
- Sensor granularity decreases from center outwards



The Phase-2 Outer Tracker Sensors

■ 2S:

- $A = 10 \times 10 \text{ cm}^2$
- Strips: $2 \times 1016 = 2032$
- Pitch: $90 \text{ }\mu\text{m}$

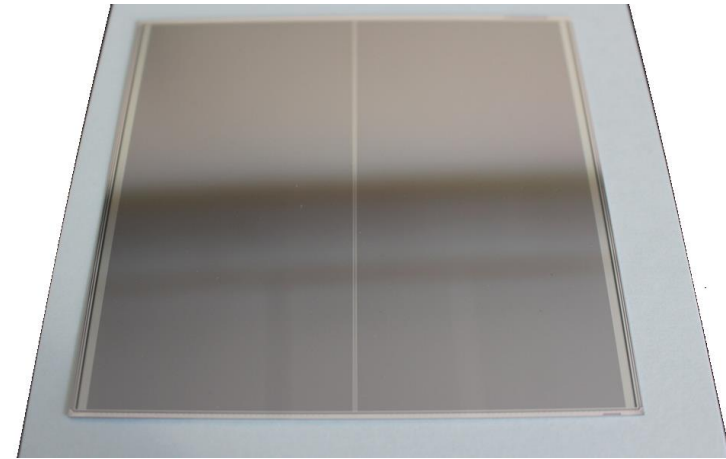
■ PS-s:

- $A = 5 \times 10 \text{ cm}^2$
- Strips: $2 \times 960 = 1920$
- Pitch: $100 \text{ }\mu\text{m}$

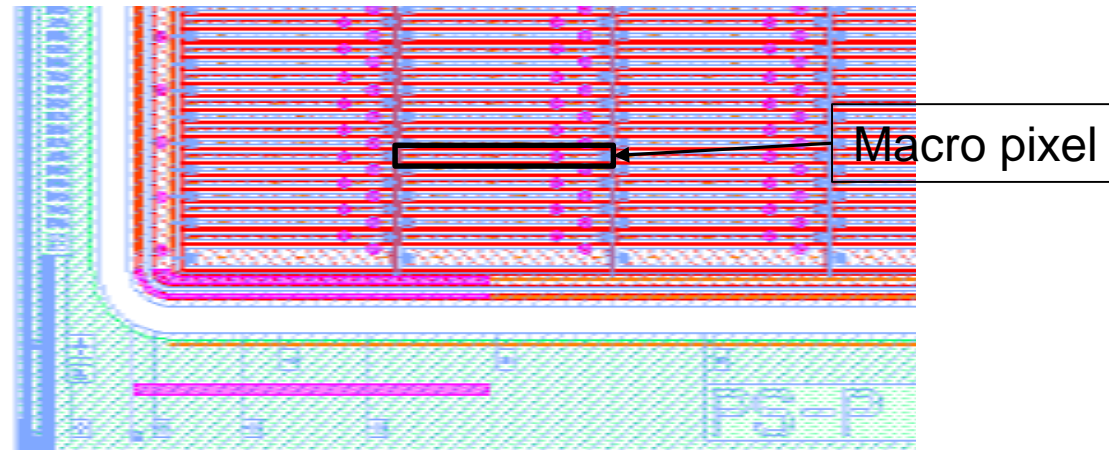
■ PS-p:

- $A = 5 \times 10 \text{ cm}^2$
- Macro pixel: $32 \times 960 = 30208$
- Pixel size: $100 \times 1500 \text{ }\mu\text{m}^2$

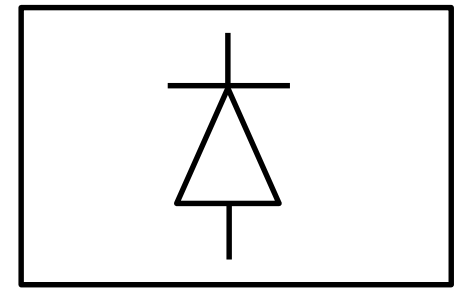
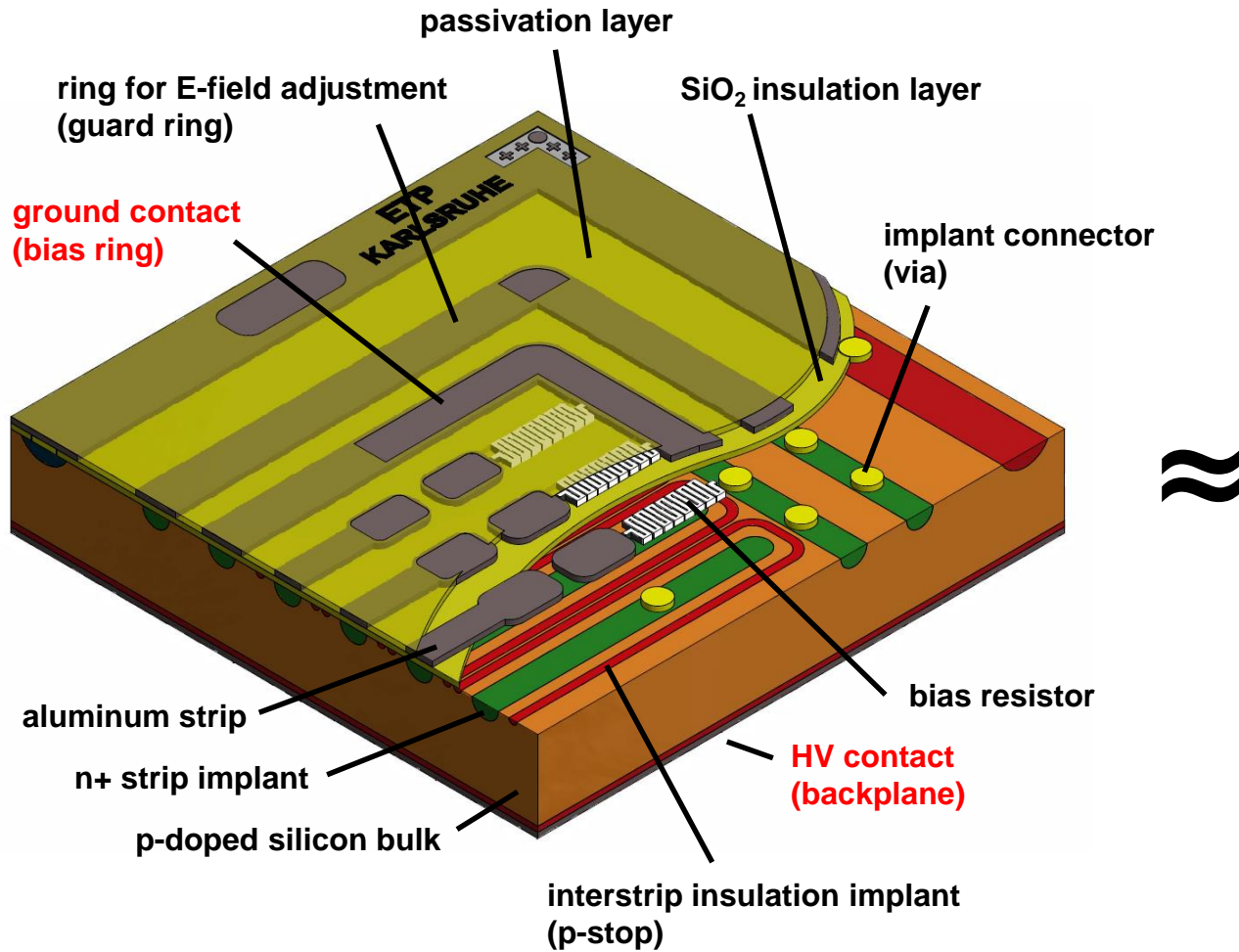
2S Sensor



PS-p Sensor



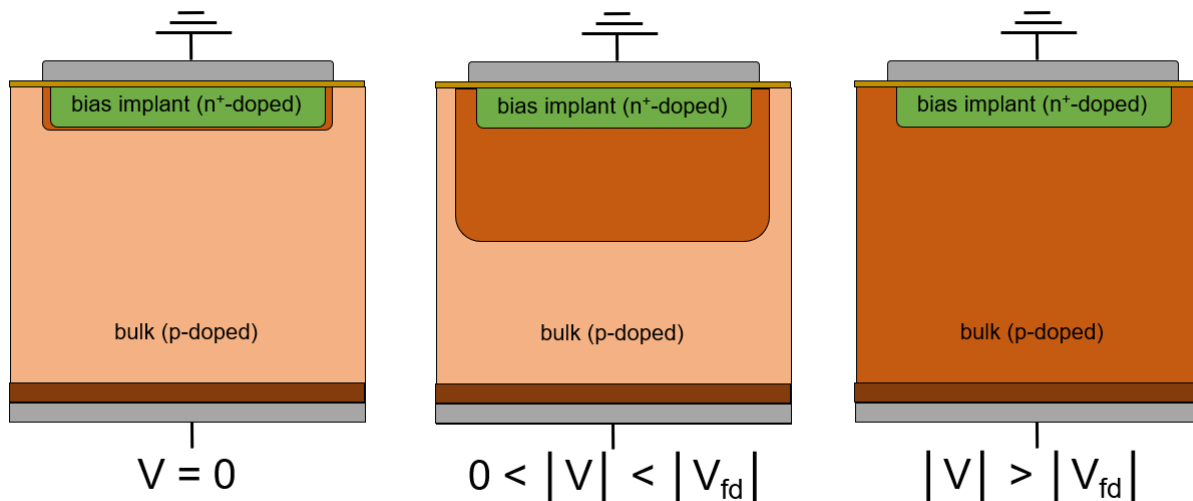
Silicon Strip Sensor - Basics



Silicon Strip Sensor - Basics

1) Operation under reverse bias at full depletion

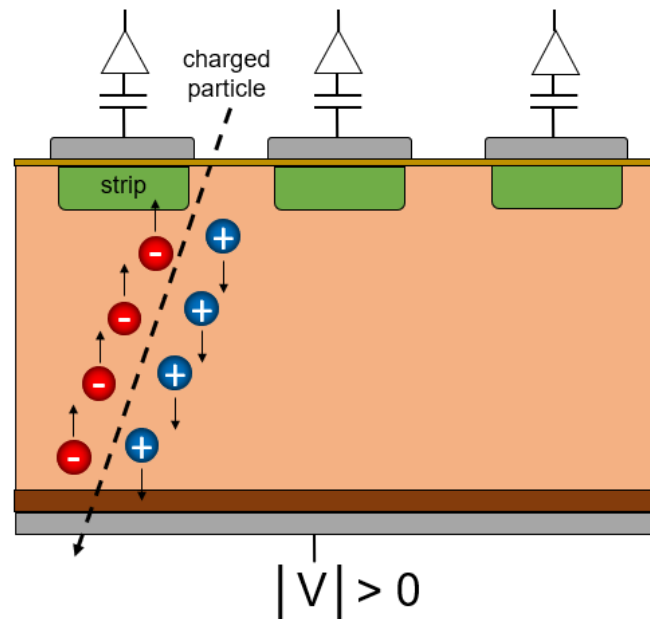
- $N_{\text{free charge carriers}} \approx O(10^8) \gg S_{\text{particle}} \approx O(10^5)$
 → full depletion is mandatory
- Leakage current I_{leak} of sensor is a significant quantity
 - $I_{\text{leak}} \sim V_{\text{bias}}$
 - $I_{\text{leak}} \sim T$ → operation temperature in tracker $T < 0$



Silicon Strip Sensor - Basics

2) Particle detection

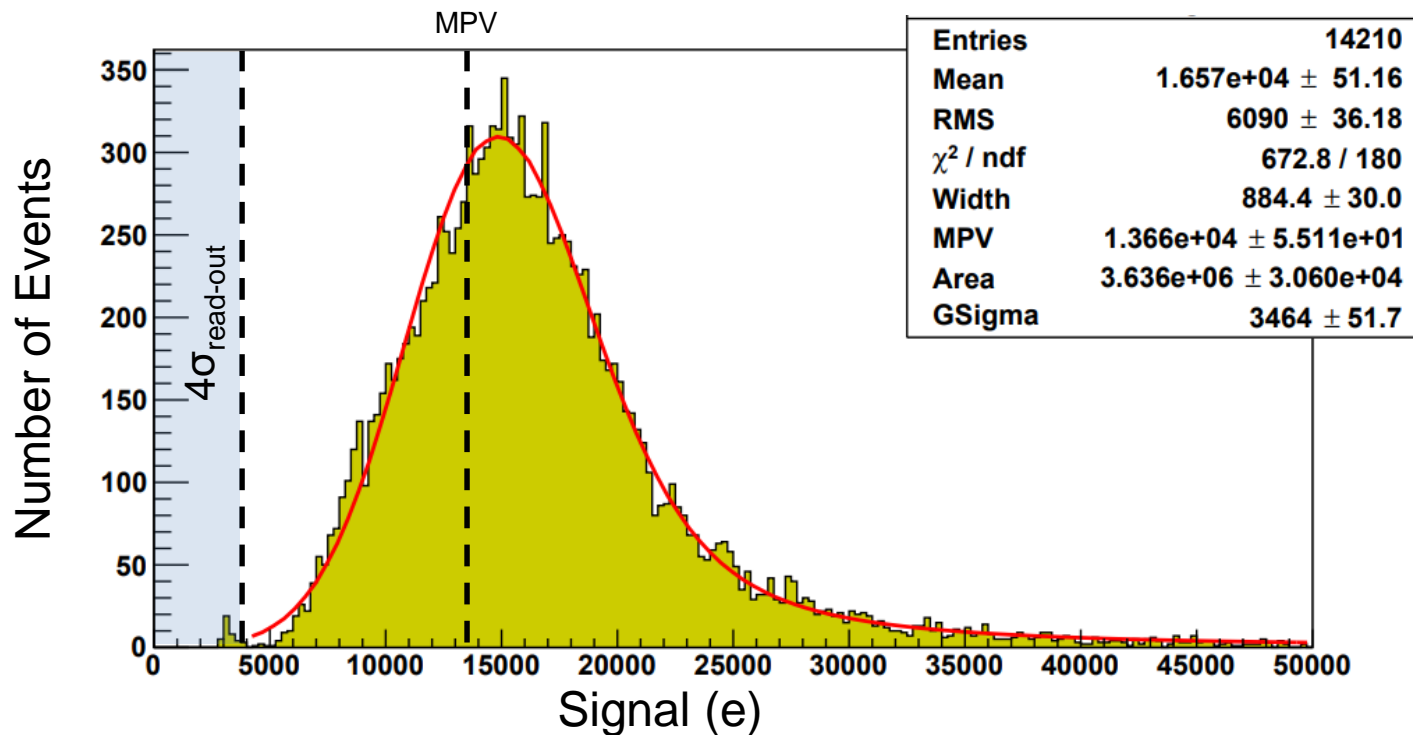
- Traversing charged particles generate eh-pairs → eh-pairs are separated by E-field → charge is collected by strips
- S_{particle} is dependent on sensor thickness ($\sim 75 \text{ eh}/\mu\text{m}$)



Silicon Strip Sensor - Basics

3) Signal

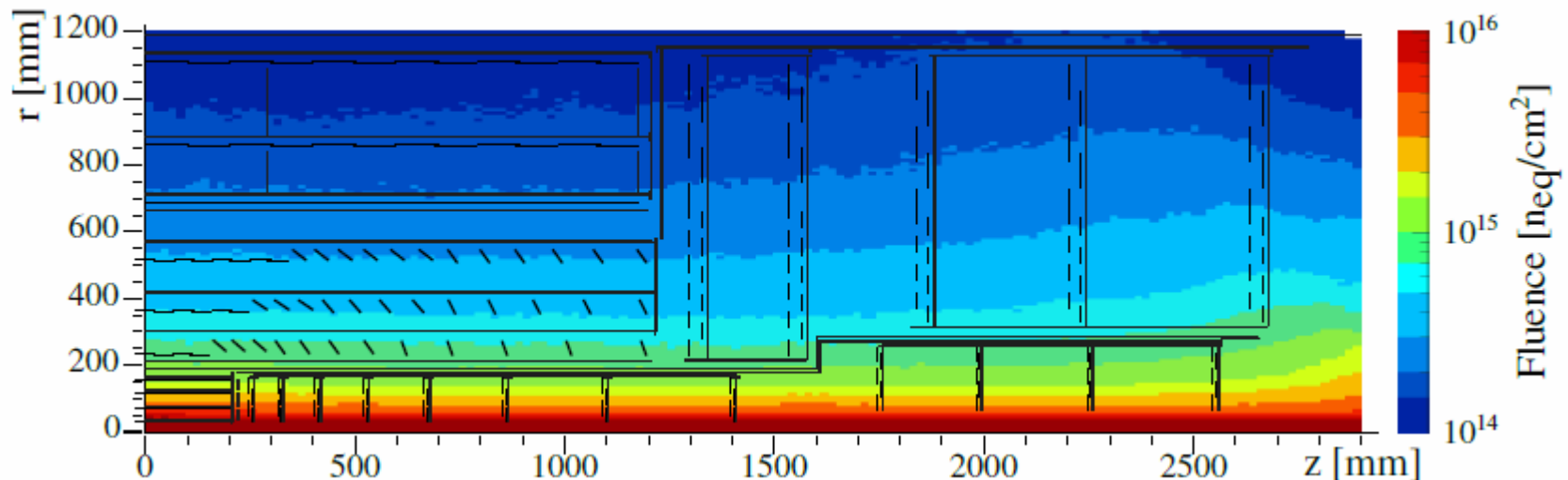
- *Signal* = most probable value (MPV) of signal distribution
- Sensor's MPV has to be well-above the noise of read-out electronics to make its operation efficient (rule of thumb: $MPV/3 > 4\sigma_{\text{read-out}}$)



Silicon Strip Sensor - Basics

4) Radiation damage

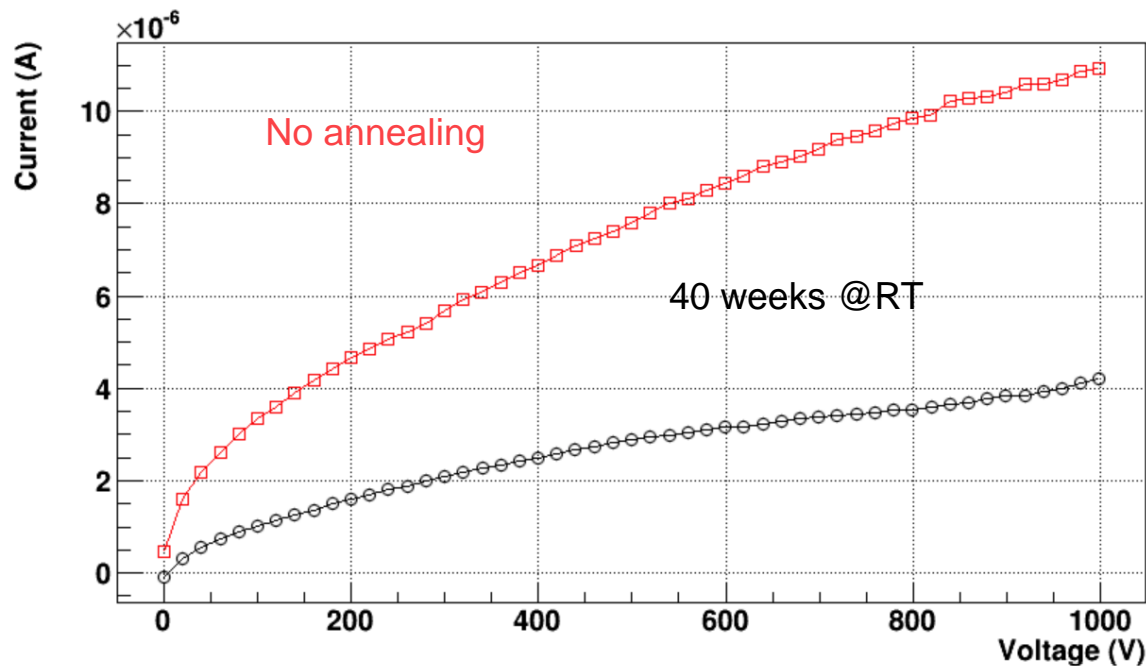
- Introduces defects in silicon lattice → additional states within the band gap → reduction of signal and increase of leakage current
- Expected maximum fluences after 10 years:
 - $\Phi_{2S} = 3 \times 10^{14} \text{ n}_{\text{eq}}\text{cm}^{-2}$
 - $\Phi_{PS} = 1 \times 10^{15} \text{ n}_{\text{eq}}\text{cm}^{-2}$



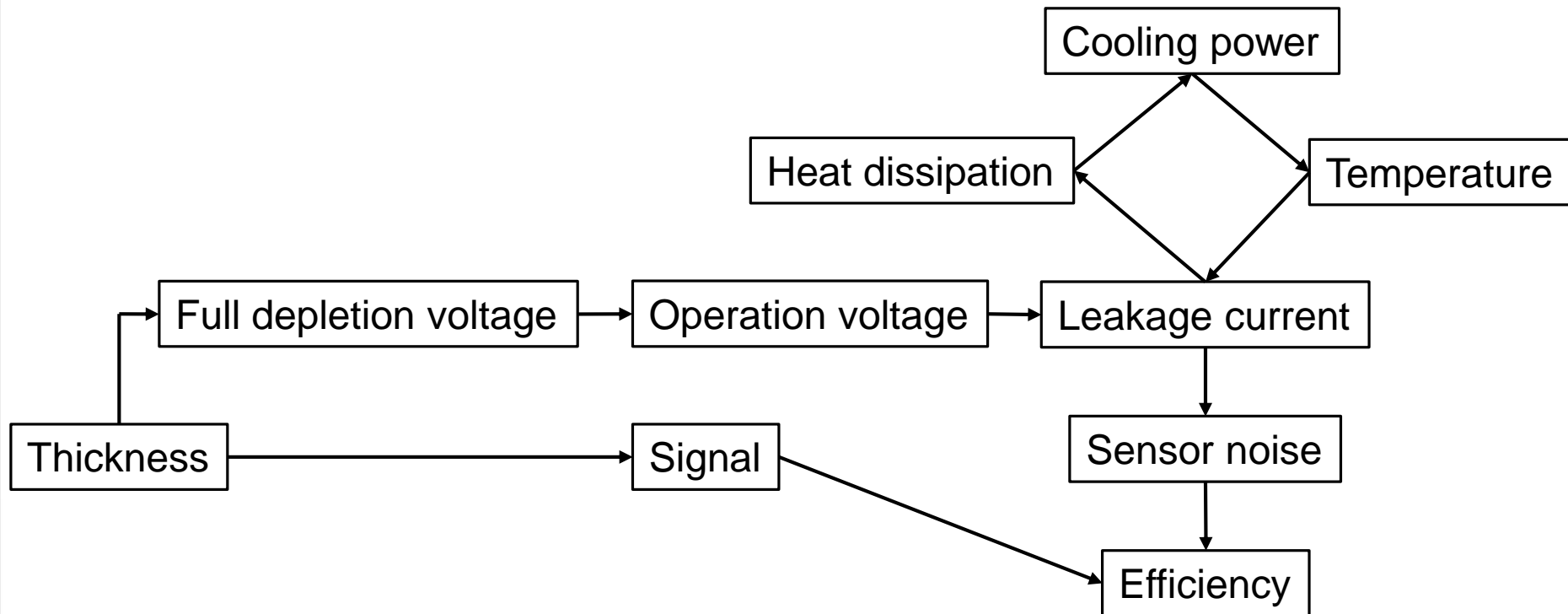
Silicon Strip Sensor - Basics

5) Annealing

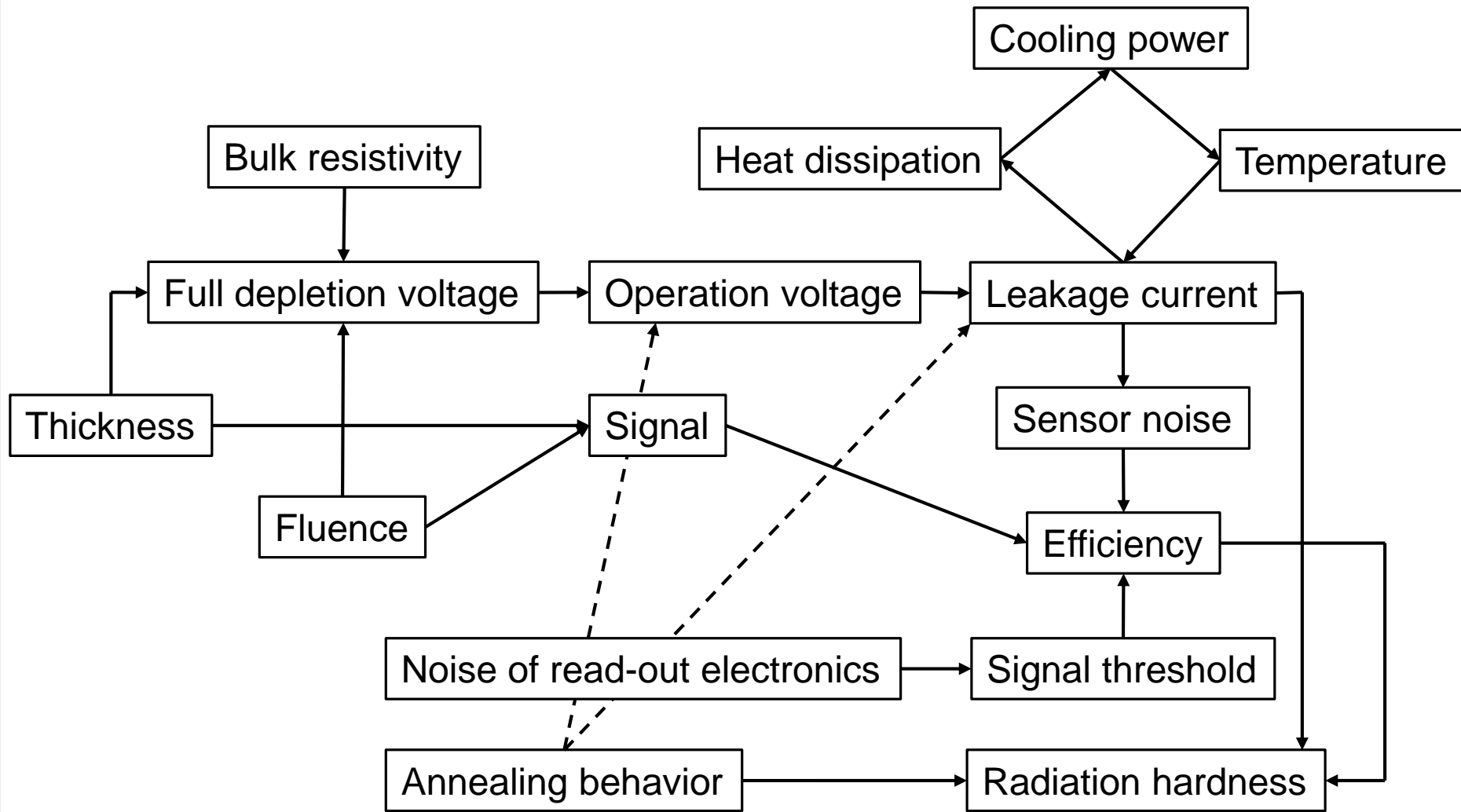
- Irradiated sensors anneal at room temperature (RT) → reduces leakage current and affects signal
- Annealing period during year-end technical stop possible



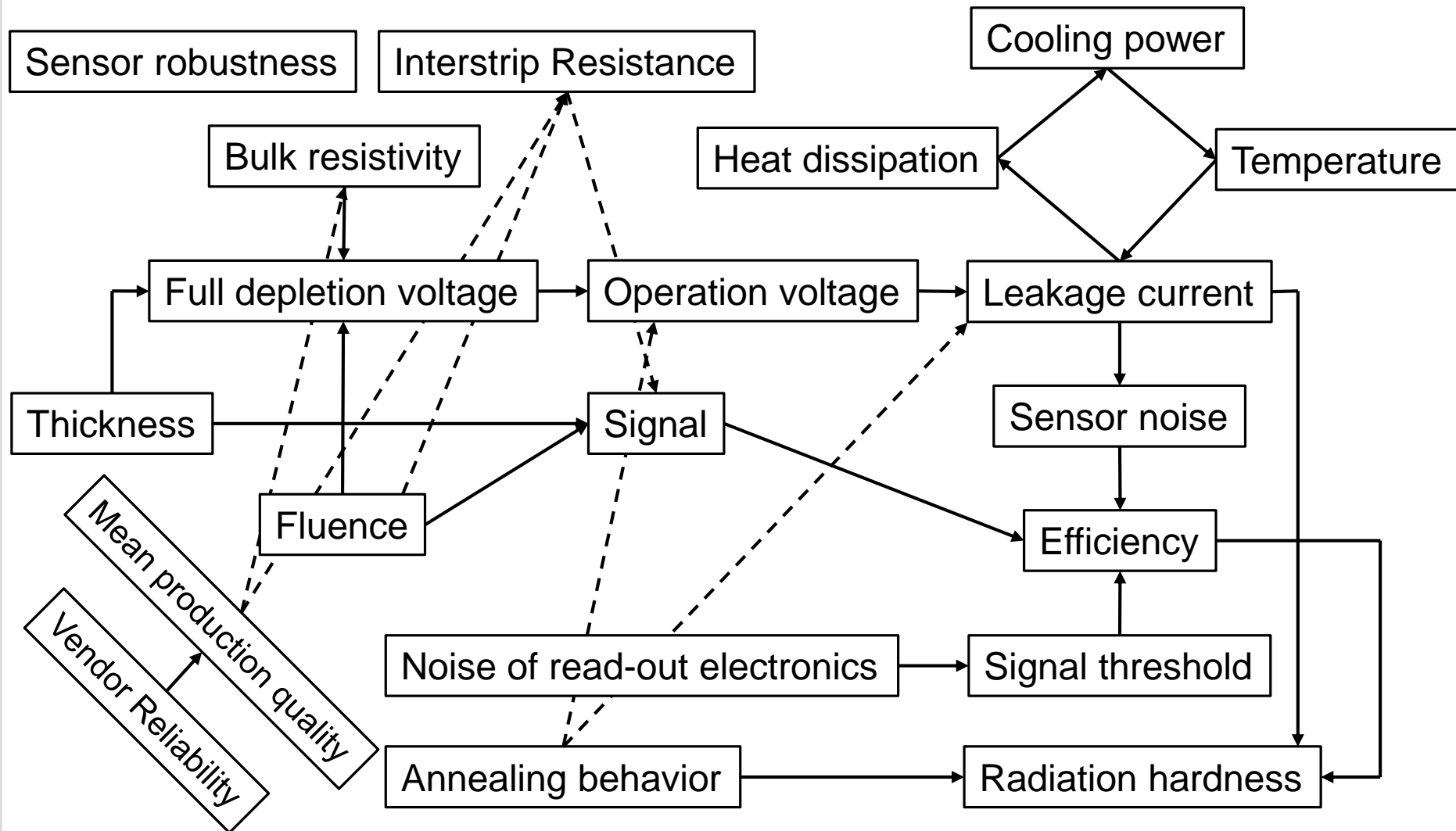
Relation of Sensor Parameters



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Relation of Sensor Parameters

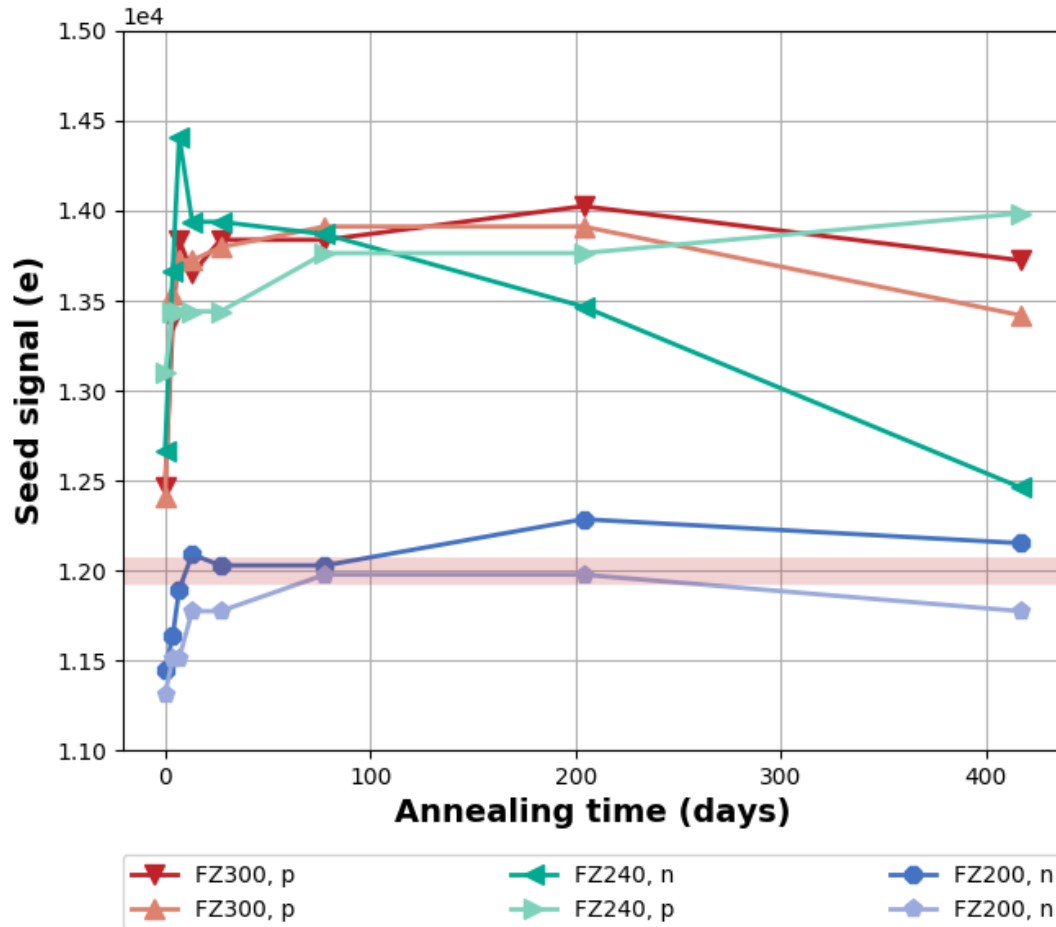


Relation of Sensor Parameters



Material Studies at ETP – Recent Results

Seed Signal vs. Annealing ($\Phi = 3e14 \text{ n}_{eq} \text{ cm}^{-2}$, $V_{bias} = 600 \text{ V}$, $T = -20^\circ \text{ C}$)

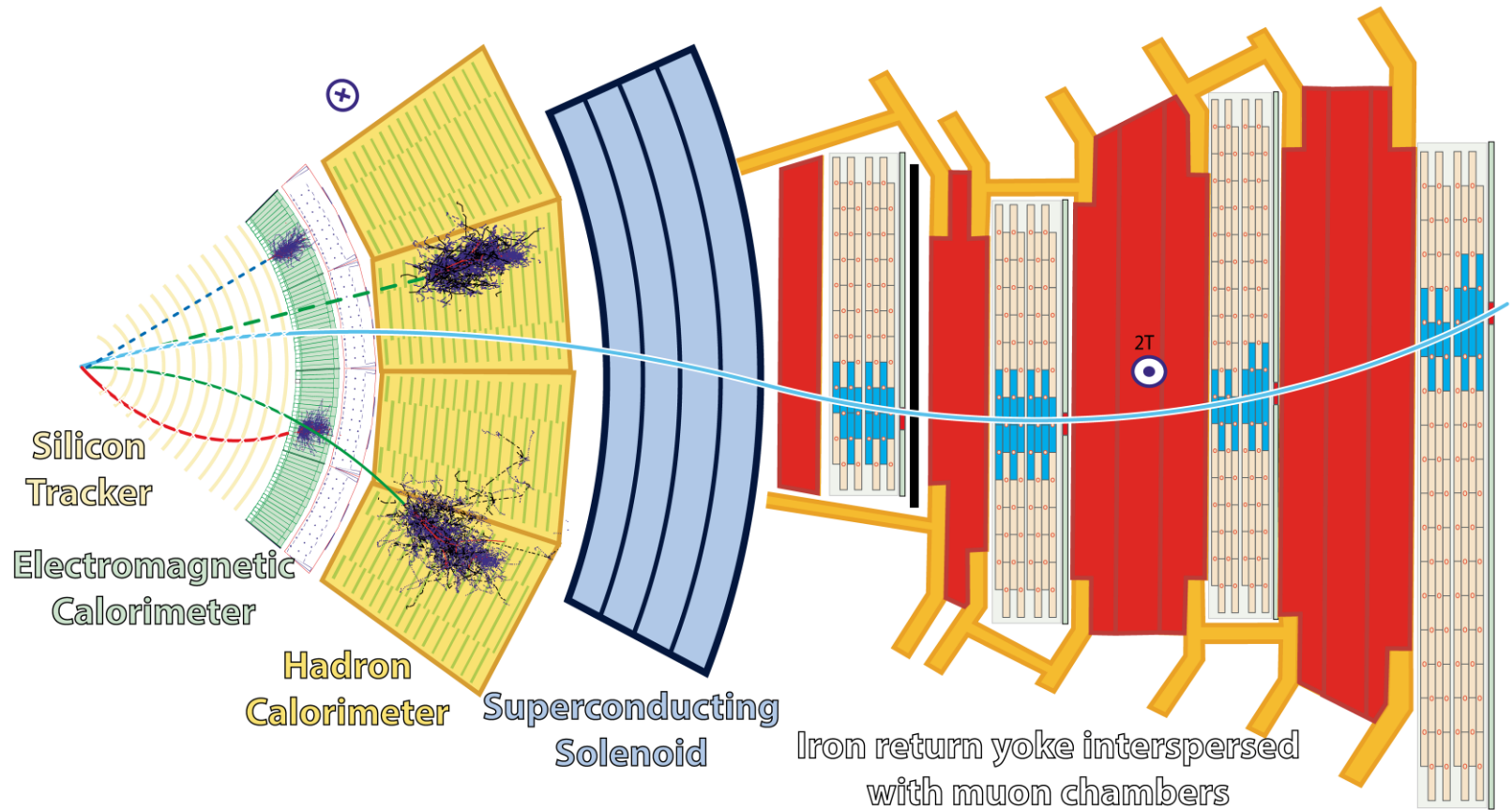


- Comparison of 200, 240 and 300 μm material for
 - $\Phi_{2S} \approx 3e14 \text{ n}_{eq} \text{ cm}^{-2}$
 - $V_{bias} = 600 \text{ V}$
- Signal of 200 μm material too low
- 240/300 μm provide similar signal and annealing characteristic at 600 V

Material Studies at ETP – Irradiation Studies

- ETP is leading institute in terms of irradiation studies due to powerful self-built setups and infrastructure
- Material decision will be made almost exclusively based on our studies
- More than 10 years of
 - Irradiation studies
 - Sensor qualification
 - Vendor qualification
- Final irradiation campaign on-going (material decision this summer)

Back Up



- Muon
- Electron
- Charged hadron (e.g. pion)
- - - Neutral hadron (e.g. neutron)
- · · Photon



